

RB425D SCHOTTKY BARRIER DIODE

FEATURES

- Small Surface Mounting Type
- Low V_F
- High Reliability

APPLICATIONS

- Low Power Rectification

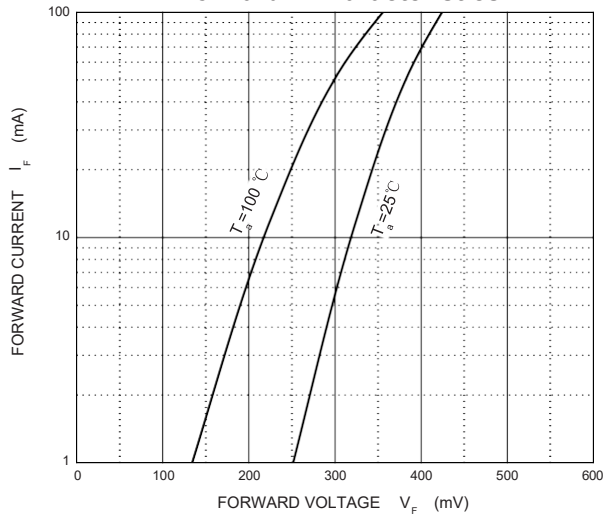
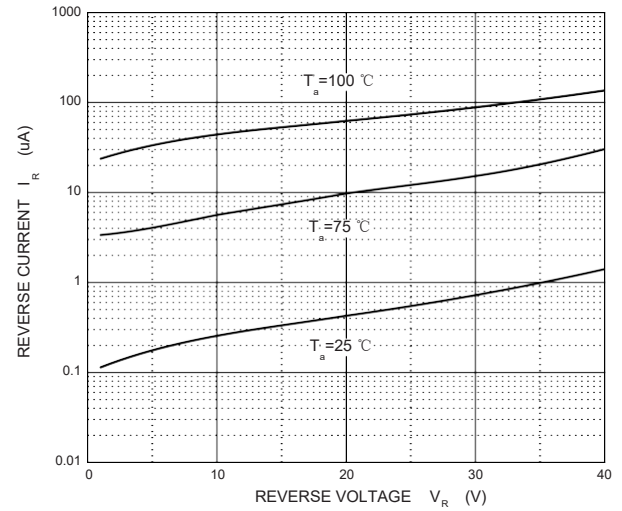
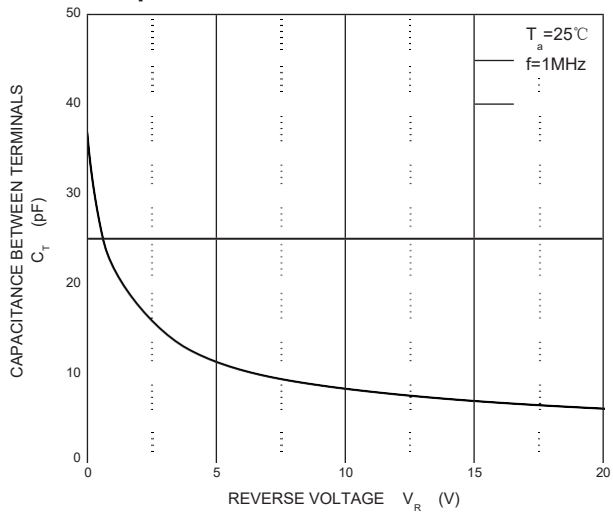


MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_R	Continuous Reverse Voltage	40	V
I_O	Continuous Forward Current	100	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current	1	A
P_D	Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	400	$^{\circ}\text{C}/\text{W}$
T_j	Operating Junction Temperature Range	-40 ~ +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55 ~ +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	40			V
Reverse current	I_R	$V_R=10\text{V}$			30	μA
Forward voltage	V_F	$I_F=100\text{mA}$			0.55	V
		$I_F=10\text{mA}$			0.34	
Total capacitance	C_{tot}	$V_R=10\text{V}, f=1\text{MHz}$		6		pF

Forward Characteristics

Reverse Characteristics

Capacitance Characteristics Per Diode

Power Derating Curve
